



1NM60

Power MOSFET

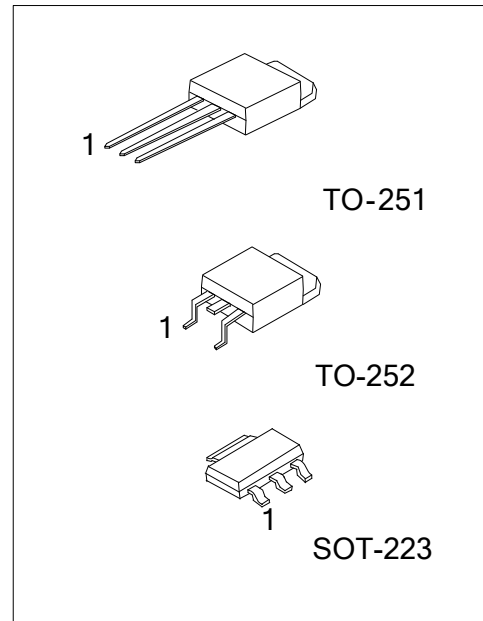
1.0A, 600V N-CHANNEL SUPER-JUNCTION MOSFET

DESCRIPTION

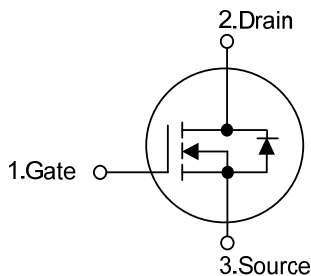
The **UTC 1NM60** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

FEATURES

- * $R_{DS(ON)} < 3.5\Omega @ V_{GS} = 10V, I_D = 0.5A$
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness



SYMBOL



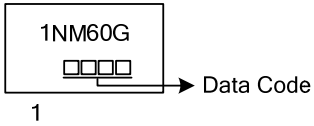
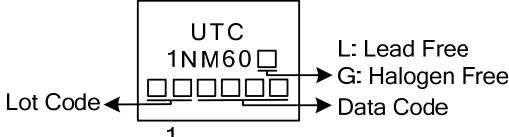
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
-	1NM60G-AA3-R	SOT-223	G	D	S	Tape Reel
1NM60L-TM3-T	1NM60G-TM3-T	TO-251	G	D	S	Tube
1NM60L-TN3-R	1NM60G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>1NM60G-AA3-R</p>	<p>(1) R: Tape Reel, T: Tube (2) AA3: SOT-223, TM3: TO-251, TN3: TO-252 (3) L: Lead Free, G: Halogen Free and Lead Free</p>
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■ MARKING

SOT-223	TO-251 / TO-252
 <p>A diagram of a SOT-223 package. The top surface is marked with "1NM60G" above three small squares. An arrow points from these squares to the text "Data Code". The number "1" is printed at the bottom of the package.</p>	 <p>A diagram of a TO-251 / TO-252 package. The top surface is marked with "UTC" above "1NM60" above four small squares. An arrow points from these squares to the text "Data Code". The number "1" is printed at the bottom of the package. An arrow points from the left side of the package to the text "Lot Code".</p> <p>L: Lead Free G: Halogen Free</p>

■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	1.0	A
	Pulsed (Note 2)	I_{DM}	4.0	A
Avalanche Current (Note 2)		I_{AR}	1.3	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	8.5	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	6.0	V/ns
Power Dissipation	SOT-223	P_D	8.0	W
	TO-251/TO-252		28	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. $L=10\text{mH}$, $I_{AS}=1.3\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD}\leq 1.0\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL CHARACTERISTICS

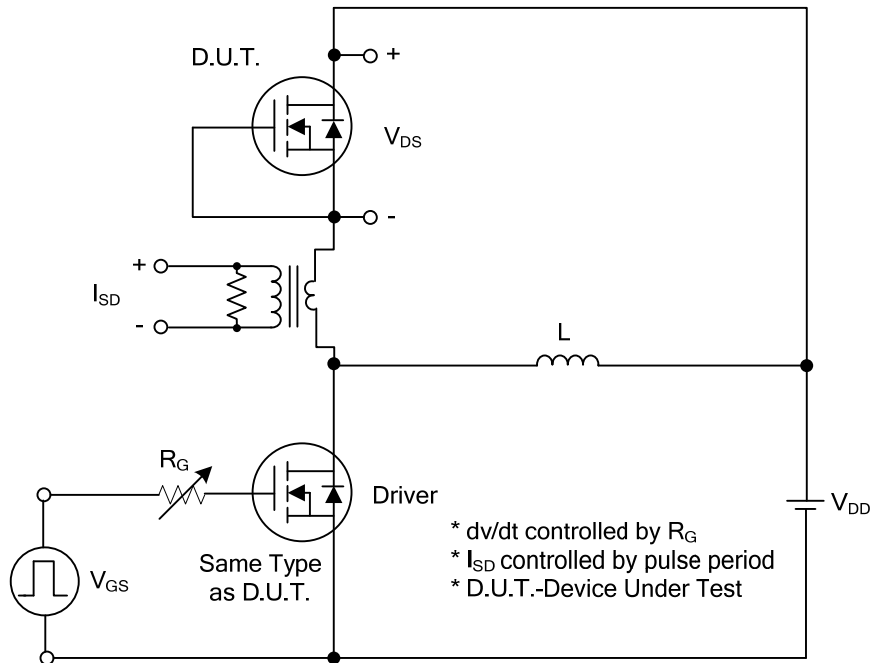
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	SOT-223	θ_{JA}	150	$^\circ\text{C}/\text{W}$
	TO-251/TO-252		110	$^\circ\text{C}/\text{W}$
Junction to Case	SOT-223	θ_{JC}	15.6	$^\circ\text{C}/\text{W}$
	TO-251/TO-252		4.46	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ($T_J=25^{\circ}\text{C}$, unless otherwise specified)

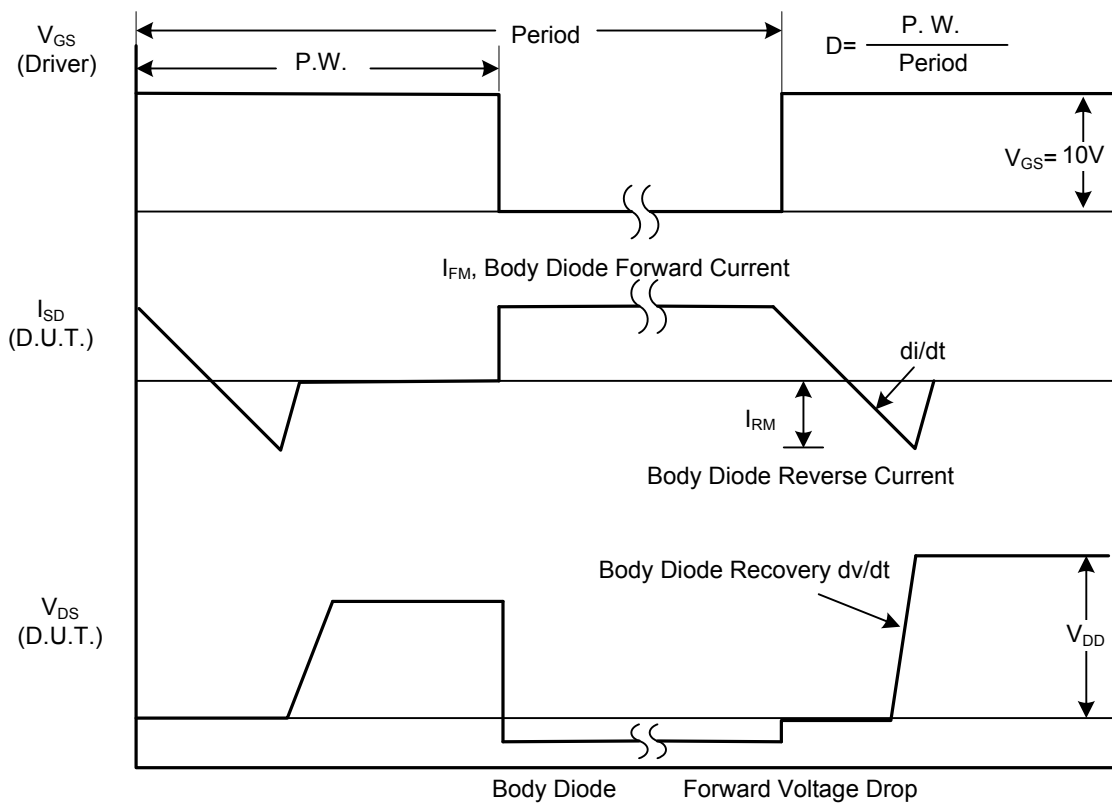
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	600			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 600V, V_{GS} = 0V$			10	μA
Gate-Source Leakage Current	Forward	$V_{GS} = +30V, V_{DS} = 0V$			+100	nA
	Reverse	$V_{GS} = -30V, V_{DS} = 0V$			-100	nA
ON CHARACTERISTICS						
Gate Threold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5		4.5	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 0.5A$			3.5	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{GS}=0V, V_{DS}=25V, f=1MHz$		113		pF
Output Capacitance	C_{OSS}			79		pF
Reverse Transfer Capacitance	C_{RSS}			8.5		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q_G	$V_{DS}=50V, V_{GS}=10V, I_D=0.5A$ $I_G=100\mu A$ (Note 1, 2)		22.5		nC
Gate to Source Charge	Q_{GS}			2.3		nC
Gate to Drain Charge	Q_{GD}			3.7		nC
Turn-ON Delay Time (Note 1)	$t_{D(ON)}$	$V_{DD}=30V, V_{GS}=10V, I_D = 0.5A,$ $R_G = 25\Omega$ (Note 1, 2)		43		ns
Rise Time	t_R			40		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			68		ns
Fall-Time	t_F			26		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				1.0	A
Maximum Body-Diode Pulsed Current	I_{SM}				4.0	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_S=1.0A, V_{GS}=0V$			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t_{rr}	$I_S=1.0A, V_{GS}=0V,$ $di_F/dt=100A/\mu s$		155		nS
Body Diode Reverse Recovery Charge	Q_{rr}			0.6		μC

Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

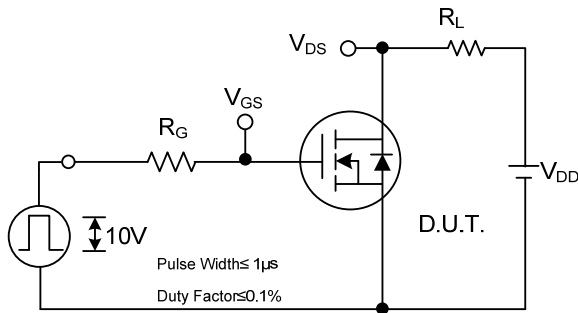


Peak Diode Recovery dv/dt Test Circuit

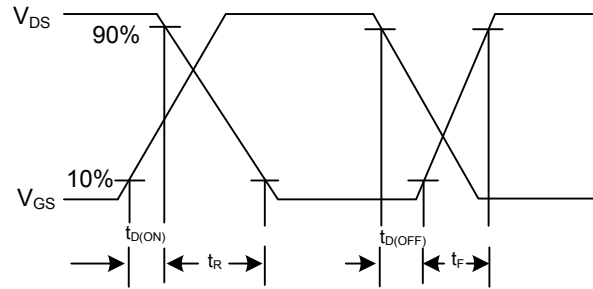


Peak Diode Recovery dv/dt Waveforms

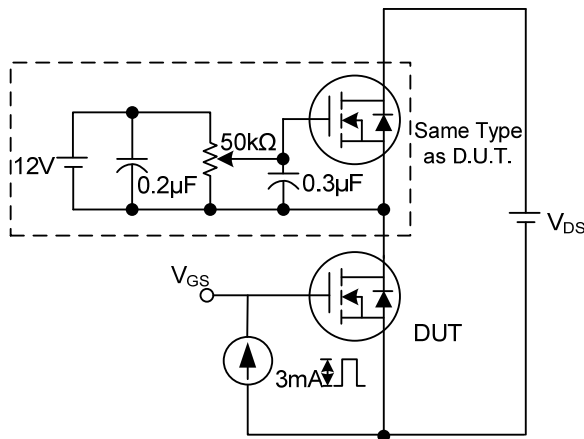
TEST CIRCUITS AND WAVEFORMS (Cont.)



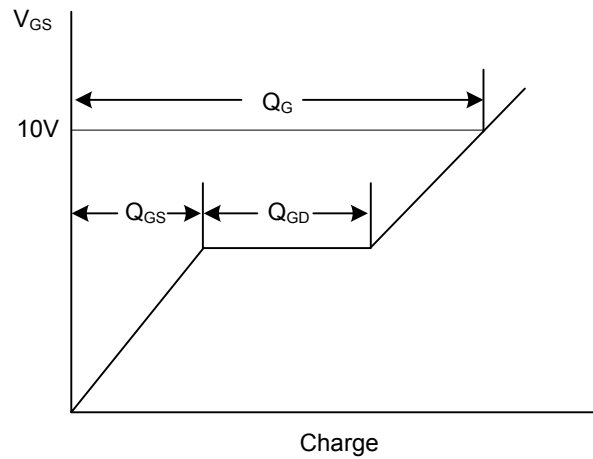
Switching Test Circuit



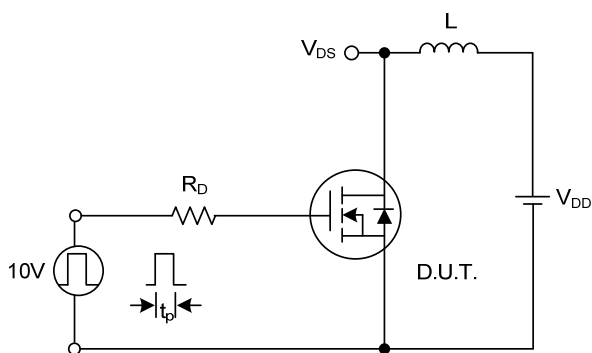
Switching Waveforms



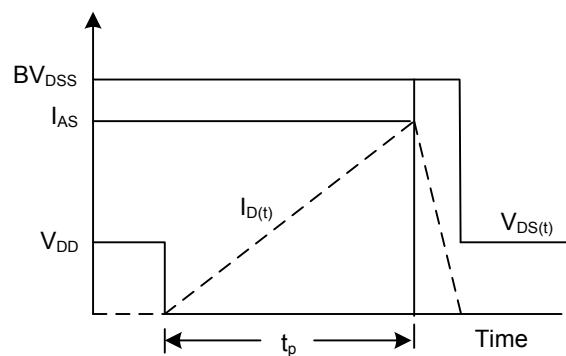
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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